

Conserved Spin and Orbital Angular Momentum Hall Current in a Two-Dimensional Electron System with Rashba and Dresselhaus Spin-orbit Coupling

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We study theoretically the spin and orbital angular momentum (OAM) Hall effect in a high mobility two-dimensional electron system with Rashba and Dresselhaus spin-orbit coupling by introducing both the spin and OAM torque corrections, respectively, to the spin and OAM currents. We find that when both bands are occupied, the spin Hall conductivity is still a constant (i.e., independent of the carrier density) which, however, has an opposite sign to the previous value. The spin Hall conductivity in general would not be cancelled by the OAM Hall conductivity. The OAM Hall conductivity is also independent of the carrier density but depends on the strength ratio of the Rashba to Dresselhaus spin-orbit coupling, suggesting that one can manipulate the total Hall current through tuning the Rashba coupling by a gate voltage. We note that in a pure Rashba system, though the spin Hall conductivity is exactly cancelled by the OAM Hall conductivity due to the angular momentum conservation, the spin Hall effect could still manifest itself as nonzero magnetization Hall current and finite magnetization at the sample edges because the magnetic dipole moment associated with the spin of an electron is twice as large as that of the OAM. We also evaluate the electric field-induced OAM and discuss the origin of the OAM Hall current. Finally, we find that the spin and OAM Hall conductivities are closely related to the Berry vector (or gauge) potential.

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I. INTRODUCTION

Spin transport electronics or spintronics in semiconductors has become a very active research field in condensed matter mainly because of its potential applications in information storage and processing and other electronic technologies [1] and also because of many fundamental questions on the physics of electron spin [2]. Spin current generation is an important issue in the emerging spintronics. Recent proposals of the intrinsic spin Hall effect are therefore remarkable [3, 4]. In the spin Hall effect, a transverse spin current is generated in response to an electric field in a metal with relativistic electron interaction (spin-orbit coupling). This effect has been considered to arise extrinsically, i.e., by impurity scattering [5]. The scattering becomes spin-dependent in the presence of spin-orbit coupling, and this gives rise to the spin Hall effect. In the recent proposals, in contrast, the spin Hall effect can arise intrinsically in hole-doped (p-type) bulk semiconductors [3] and also in electron-doped (n-type) semiconductor heterostructures [4] due to intrinsic spin-orbit coupling in the band structure. This intrinsic spin Hall effect offers an exciting possibility of pure electric driven spintronics in semiconductors, where spin-orbit coupling is relatively strong and which can be more readily integrated with well-developed semiconductor electronics.

A large number of theoretical papers have been written

addressing various issues about the intrinsic spin Hall effect. In [6], a systematic semi-classical theory of spin transport is presented, resolving a discrepancy between the prediction of [3] and the Kubo formula result. In [7], an orbital-angular-momentum (OAM) Hall current is predicted to exist in response to an electric field and is found to cancel exactly the spin Hall current in the spin Hall effect. In [8], however, *ab initio* relativistic band structure calculations show that the OAM Hall conductivity in hole-doped semiconductors is one order of magnitude smaller than the spin Hall conductivity, indicating no cancellation between the spin and OAM Hall effects in bulk semiconductors because of the orbital quenching by the cubic crystalline anisotropy. There is also an intensive debate about whether the intrinsic spin Hall effect remains valid beyond the ballistic transport regime [9, 10, 11]. On the other hand, experimental measurements of large spin Hall effects for the Rashba two-dimensional electron gas and for n-type bulk semiconductors have just been reported [12, 13], although more work is needed to firmly establish the intrinsic or extrinsic nature of the results.

At present, an urgent current issue in spintronics research is about the appropriate definition of the spin current [14, 15, 16, 17, 18]. In almost all previous studies of the intrinsic spin Hall effect, the spin current is intuitively defined as the expectation value of the spin and velocity operators, namely, $\frac{1}{2}f\mathbf{v};s_zg$, where $f;g$ is the anticommutator defined by $fA;Bg = AB + BA$. Similarly, the OAM current is defined as the expectation value of $\frac{1}{2}f\mathbf{v};L_zg$. Here, s_z and L_z are the z-component of spin and OAM operators, respectively, and \mathbf{v} is the velocity operator. However, this conventionally defined spin

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(OAM) current is not conserved in systems with spin-orbit interaction [6]. Consequently, many fundamental questions on the intrinsic spin Hall effect in semiconductors remain unresolved. Very recently, in Ref.16, a proper definition of the conserved effective spin current is established for systems with spin-orbit coupling, and the conserved spin current density is defined as

$$\mathbf{J}_s = \mathbf{J}_s + \mathbf{P}; \quad (1)$$

where $\mathbf{J}_s = \text{Re}[\frac{1}{2}f\nabla; s_z g]$ is conventional spin current density and \mathbf{P} is the torque dipole density which arise from spin torque $\mathbf{T}_z^s = \text{Re}[\frac{1}{i}\nabla; [s_z; H_0]]$ where H_0 is the Hamiltonian of the system. The commutator $[f;]$ is defined by $[A; B] = AB - BA$. The effective spin current density \mathbf{J}_s then satisfies the standard continuity equation [16] of $\frac{\partial S_z}{\partial t} + \nabla \cdot \mathbf{J}_s = 0$ where the spin density is defined by $S_z = \nabla \cdot \mathbf{s}_z$. A derivation of the effective spin continuity equation in Rashba-Dresselhaus system is given in Appendix A. Within this definition of the effective spin current, the unphysical intrinsic spin Hall effect in insulators with localized orbitals vanishes, and the Onsager relation between the spin Hall effect and inverse spin Hall effect is ensured. [6] Furthermore, this new definition of the spin current predicts opposite signs of spin Hall coefficients for a couple of semiconductor models such as the Rashba and k-cubed Rashba Hamiltonians. [16]

In this paper, we extend the theory proposed in Ref. 16 to two-dimensional electron system with both Rashba and Dresselhaus spin-orbit coupling. Furthermore, we introduce the concept of the effective OAM current by including an OAM torque correction term, and investigate the OAM Hall effect in both pure Rashba system and systems with Rashba-Dresselhaus spin-orbit coupling. We derive the effective OAM continuity equation for the Rashba-Dresselhaus system (Appendix B). Also in this paper, we argue that in a pure Rashba system, though the OAM Hall conductivity is found to exactly cancel the spin Hall conductivity, there nevertheless would be nonzero magnetization current and finite magnetization at the sample edges because the magnetic dipole moment associated with spin angular momentum is twice as large as that of the OAM. Finally, we find that there are interesting relations between the Berry vector potential and the spin and OAM Hall conductivities.

II. MODEL HAMILTONIAN AND LINEAR RESPONSE CALCULATION

A. Rashba-Dresselhaus Hamiltonian

For a two-dimensional electron gas (2DEG) confined in a semiconductor heterostructure, two major spin-orbit (SO) interaction terms are usually present. One is the Rashba term [19],

$$H_R = \frac{\hbar}{2m} (\mathbf{p} \times \mathbf{e}) \cdot \mathbf{p}; \quad (2)$$

which stems from the structural inversion asymmetry. Here, $\mathbf{e} = (e_x; e_y)$ and \mathbf{e}_z are the three Pauli matrices. The other is the Dresselhaus SO coupling which results from the bulk inversion asymmetry, if the heterostructure is made of semiconductors without spatial inversion symmetry such as semiconductors in the zincblende structure [20]. The Dresselhaus term is given by

$$H_D = \frac{\hbar}{2m} (\mathbf{p}_x \times \mathbf{p}_y \cdot \mathbf{e}_z); \quad (3)$$

Therefore, the full Hamiltonian for the 2DEG with Rashba-Dresselhaus SO coupling can be written as

$$H_0 = \frac{p^2}{2m} + H_R + H_D; \quad (4)$$

where m is the effective mass of the electrons in the 2DEG. Interestingly, though the Dresselhaus coupling coefficient is fixed for a given structure, the Rashba coupling strength can be tuned by a gate voltage by up to 50% [21], thereby providing an opportunity to study the interesting interplay between both types of the SO coupling. The Hamiltonian has been solved exactly by several authors. The eigenstates can be written as

$$|jnk\rangle = \frac{1}{\sqrt{2}} e^{i\phi(k)} |n\rangle; \quad (5)$$

where $n = 1$ is band index and

$$\tan \phi(k) = \frac{k_y}{k_x} \frac{k_x}{k_y}; \quad (6)$$

The corresponding eigenenergies is given by

$$E_{nk} = \frac{\hbar^2}{2m} k^2 - nk \phi(k); \quad (7)$$

where $\mathbf{k} = (k_x; k_y)$, $k = |\mathbf{k}|$, $\tan \phi(k) = k_y/k_x$, $\cos \phi(k) = \frac{k_x}{k}$, $\sin \phi(k) = \frac{k_y}{k}$, and $\phi(k) = \arctan(\frac{k_y}{k_x})$. It can be proved that the difference of two Fermi momenta $\sim k_F$ is given by $(k_F^+ - k_F^-) = 2m \phi(k) = \sqrt{2}$. The band structure consists of two energy bands which are degenerate at the centre of the 2D momentum space $\mathbf{k} = 0$, as schematically illustrated in the left panel of Fig. 1(a). The spins associated with the eigenstates all lie in the xy plane, as shown in the right panel of Fig. 1(a) and in the left panel of Fig. 1(b).

B. Spin Hall conductivity

Let us consider an uniform electric field E applied in the y-direction. The total Hamiltonian in this case is given by $H = H_0 + eEy$, where e is the electron charge. Let us treat the term eEy as a small perturbation. To determine the spin transport coefficient, we start with

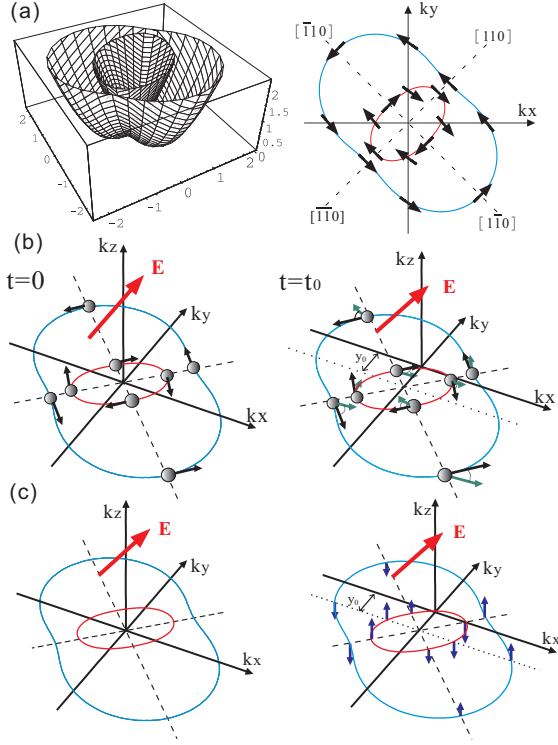


FIG. 1: (Coloronline) (a) The schematic bandstructure of the Rashba-Dresselhaus spin-orbit coupling system with $j_x \neq j_y$. The outer sheet is for $n = +1$ and the inner sheet, for $n = -1$. The two sheets touch at $k = 0$. If $\gamma = 0$, the sheets become degenerate at line $k_x = k_y$ (see, also, Fig. 1 in [23]). The right panel is the top view of the two bands. The arrows labeled on the two bands denote the spin directions of the associated k -points, respectively. (b) Initially, the spins are in the xy -plane (the left panel). At a short time t_0 after an external electric field E (indicated as the large horizontal (red) arrow) is applied along the y axis, the bands move in the $-k_y$ direction with the distance $k_y = eEt_0/\hbar$ (see Subsec. II E). Each spinor feels an effective magnetic field and will do precession. For $k_x > 0$, the spins tend to tilt down and for $k_x < 0$, the spins tend to tilt up (the right panel). The z component of the spin is given by $\hbar s_z = eE \sim (\gamma^2/\hbar^2) \cos \theta = 4nk^2/\hbar^2$. (c) Before an external electric field is applied, all the eigenstates carry zero orbital angular momentum (OAM), i.e., $\hbar L_z i_0 = 0$ (see Subsec. II E). When the electric field is turned on, the z component of the OAM is induced as shown in the right panel (small vertical arrows). A linear response calculation would give the z component as: $\hbar L_z i = eE \sim (\gamma^2/\hbar^2)^2 \cos \theta = 4nk^2/\hbar^2$.

the linear response Kubo formula in the clean limit. The conventional spin Hall conductivity is [22]

$$s_{xy}^0 = \frac{e}{V} \sum_{n \neq n^0} \sum_k [\mathbf{f}_{nk} \cdot \mathbf{f}_{n^0k}] \frac{\text{Im} [\hbar \mathbf{k} j_x^{s_z} \hbar^0 k i \hbar^0 k j_y \hbar k i]}{(\mathbf{E}_{nk} \cdot \mathbf{E}_{n^0k})^2}; \quad (8)$$

where $j_x^{s_z} = 1/2 f v_x / s_z g$ is the usual spin current operator, $v(k) = \partial H_0(k) / \partial k$, $H_0(k) = e^{ik} H_0 e^{-ik}$, $s_z = \hbar/2 \sigma_z$, $\hbar k i$ is the eigenstate of the n th band with momentum k , and f_{nk} is the Fermi-Dirac distribution. The index $n \neq n^0$ denotes no intraband transition. Similarly, the spin torque response coefficient can also be obtained [16]:

$$s(q) = \frac{ie}{V} \sum_{n \neq n^0} \sum_k [\mathbf{f}_{nk} \cdot \mathbf{f}_{n^0k+q}] \frac{\hbar \mathbf{k} j_s(k; q) \hbar^0 k + q i \hbar^0 k + q j_y(k; q) \hbar k i}{(\mathbf{E}_{nk} \cdot \mathbf{E}_{n^0k+q})^2}; \quad (9)$$

where $s(k; q) = \frac{1}{2} [s(k) + s(k+q)]$, $v(k; q) = \frac{1}{2} [v(k) + v(k+q)]$ with $s = \frac{1}{\hbar} [s_z; H_0]$. In the above equation, s_{xy}^0 is the transport coefficient of conventional spin current and s_{xy}^s can be determined from the dc response of the spin torque dipole: $\mathbf{P} = \text{Re} [\mathbf{r}_q(q)] \hbar^0 E$, namely, $s_{xy}^s = \text{Re} [\mathbf{r}_y(q) = \partial \mathbf{r}_x / \partial k] \hbar^0$ [16]. Here $\mathbf{r}(q)$ is the response coefficient of spin torque to an electric field with finite wavevector q . Before doing summation in the above Kubo formula, we expand the term inside the summation to the first order of q . At zero temperature, $f_{n^0k+q} = f_{n^0k} + q \cdot \partial f_{n^0k} / \partial \mathbf{E}_{n^0k}$, where the first term is a step function while the second term was involved with a Dirac delta function. We assume that the two bands are all occupied by the electrons and the Fermi energy is larger than the SO splitting. The spin Hall conductivity is

$$s_{xy} = s_{xy}^0 + s_{xy}^s; \quad (10)$$

which is the linear response of the conserved effective spin current J_s to the electric field [16]. It is straightforward to calculate the spin Hall conductivity (the detailed derivation is given in Appendix C). We find that $s_{xy}^0 = \text{sign}(\gamma^2/\hbar^2) e/8$ is the conventional spin Hall conductivity and $s_{xy}^s = \text{sign}(\gamma^2/\hbar^2) e/4$ is the conductivity due to the spin torque correction. Therefore, the spin Hall conductivity defined as the response of the conserved effective spin current is:

$$s_{xy} = \begin{cases} \frac{e}{8}; & \gamma^2 > \gamma_c^2 \\ 0; & \gamma^2 = \gamma_c^2 \\ \frac{e}{4}; & \gamma^2 < \gamma_c^2; \end{cases} \quad (11)$$

which is independent of the carrier density. Remarkably, with the spin torque correction term s_{xy}^s included, the sign of the effective spin Hall conductivity is opposite to the conventional spin Hall conductivity reported in [23] and [24].

C. Orbital angular momentum Hall conductivity

The usual OAM current operator was introduced as

$$j_x^{l_0} = \frac{1}{2} f v_x / L_z g; \quad (12)$$

where L_z is the z component of the OAM operator. In the Rashba Hamiltonian and with this definition of the OAM current, the spin Hall effect is always accompanied by the OAM Hall effect which was first noted by Zhang and Yang [7]. In a SO system, such a definition has the same problems as the conventional spin current operator because the OAM current is not a conserved quantity. Therefore, we derive the continuity equation for the effective OAM current (see Appendix B). We find $\frac{\partial L_z}{\partial t} + \nabla \cdot \mathbf{J} = T_z^o$, where $L_z = \int V L_z$ is the z component of the OAM density, $J_o = \text{Re}[\int \mathbf{j}^o]$ is the OAM current density and $\mathbf{j}^o = \frac{1}{2} f \mathbf{v}; L_z \mathbf{g}$. $T_z^o = \text{Re}[\int \mathbf{v} \cdot \mathbf{o}]$ is the torque density, where $\mathbf{o} = \frac{1}{i\hbar} [\mathbf{L}_z; H_0]$. In analogue to the conserved effective spin current operator proposed in [16], the average torque in the bulk is zero, and hence we have $\frac{1}{V} \int dV T_z^o = 0$. The torque density can be written as the divergence of torque dipole density $\mathbf{P}^o(\mathbf{x})$, i.e., $T_z^o = \nabla \cdot \mathbf{P}^o(\mathbf{x})$. Substituting $T_z^o = \nabla \cdot \mathbf{P}^o$ into continuity equation of OAM, we obtain $J_o = J_o + \mathbf{P}^o$ as the effective OAM current. The torque dipole density vanishes outside the bulk, and we can write $\int_V dV \mathbf{P}^o = \int_V dV (\mathbf{x} \times \mathbf{r} \cdot \mathbf{P}) = \int_V dV \mathbf{x} T_z^o$. Therefore, the unique form of torque dipole density is $\mathbf{P}^o = \text{Re}[\int \mathbf{v}(\mathbf{x} \cdot \mathbf{o})]$. In short, we may define an effective OAM current operator:

$$\hat{J}_o = \frac{dx}{dt} L_z + \mathbf{x} \cdot \mathbf{o}; \quad (13)$$

It has an extra term $\mathbf{x} \cdot \mathbf{o}$ which is the correction term due to the OAM torque. The corresponding OAM current density $J_o = \text{Re}[\int \mathbf{v}(\mathbf{x}) \hat{J}_o]$ defined as the expectation value of this current operator satisfies the standard continuity equation of $\frac{\partial L_z}{\partial t} + \nabla \cdot \mathbf{J} = 0$. As for the spin Hall conductivity [16], the OAM Hall conductivity has two parts:

$$\sigma_{xy}^o = \sigma_{xy}^o + \sigma_{xy}^i; \quad (14)$$

where the first term is the usual OAM Hall conductivity and the second term comes from the OAM torque correction. Thus, the OAM Hall conductivity can be calculated from Eq. (8) and Eq. (9) by substituting $j_x^{S_z}$ and $j_y^{S_z}$ with j_x^o and $j_y^o = \frac{1}{i\hbar} [\mathbf{L}_z; H_0]$, respectively. It can be shown (Appendix C) that the OAM Hall conductivity defined as the linear response of the effective OAM current is:

$$\sigma_{xy}^o = \begin{cases} \frac{2 + \frac{2}{2}}{2} \frac{e}{8}; & 2 > 2 \\ 0; & 2 = 2 \\ \frac{2 + \frac{2}{2}}{2} \frac{e}{8}; & 2 < 2 \end{cases} \quad (15)$$

which is a function of the ratio $\frac{2}{2}$ and is also independent of the carrier density.

D. Berry vector potential and Hall conductivity

When the Hamiltonian of a physical system is parameterized by periodically changing environment, the state

ket of system will travel on a close path and return to initial state ket after a period. The final state ket must coincide with initial state vector, apart from a phase factor. Berry [25] has shown that the state ket will acquire an additional phase factor as the system undergoes the adiabatic evolution. The phase factor accompanying the adiabatic evolution is called Berry phase. Berry phase cannot be removed by any gauge transformation for a closed path [26]. In solids, the Bloch state also acquire a Berry phase if the applied perturbation can make a constraint such that \mathbf{k} travels adiabatically on a closed path in the Brillouin zone [27]. The Berry phase of Bloch states $j\mathbf{k}$ for a closed path C can be expressed by

$$\gamma_n = \oint_C \mathbf{A}_n(\mathbf{k}) \cdot d\mathbf{l}; \quad (16)$$

where $\mathbf{A}_n(\mathbf{k}) = \hbar \mathbf{k} j(\mathbf{i}) \frac{\partial}{\partial \mathbf{k}} j\mathbf{k}$ is defined as Berry vector potential (or Berry connection). Berry curvature is defined as $\kappa_n = \nabla_{\mathbf{k}} \cdot \mathbf{A}_n$. The Berry vector potential and curvature are the salient characteristic of energy band structure and hence have important applications in transport properties of carriers. It has been shown that the equation of motion of Bloch electron has an extra anomalous velocity in terms of Berry curvature of Bloch states [28]. In bulk p-type semiconductors with spin-orbit coupling, the existence of \mathbf{k} -space magnetic monopole (Berry curvature) in the degeneracy point of band structure results in a transverse force exerting on spin [3]. The connection between the dissipationless spin Hall conductivity and Berry curvature has been shown in [29]. Here we further show that in two-dimensional Rashba-Dresselhaus systems, we can write the spin Hall and OAM Hall conductivities in terms of Berry curvature and vector potential.

With the eigenstates $j\mathbf{k}$ given by Eq. (5), we can prove that the matrix element $\hbar \mathbf{k} j_y j\mathbf{k}$ satisfies the following relation (for $n^0 \neq n$):

$$\hbar \mathbf{k} j_y j\mathbf{k} = \frac{i}{\hbar} (E_{n\mathbf{k}} - E_{n^0\mathbf{k}}) \hbar \mathbf{k} j(\mathbf{i}) \frac{\partial}{\partial \mathbf{k}_y} j\mathbf{k} \quad (17)$$

where $\hbar \mathbf{k} j(\mathbf{i}) \frac{\partial}{\partial \mathbf{k}_y} j\mathbf{k} = \frac{1}{2} \frac{\partial}{\partial \mathbf{k}_y}$. The Berry vector potential is then given by

$$\mathbf{A} = \hbar \mathbf{k} j(\mathbf{i}) \frac{\partial}{\partial \mathbf{k}} j\mathbf{k} = \frac{1}{2} \frac{\partial}{\partial \mathbf{k}}; \quad (18)$$

Substituting Eqs. (17), and (18) into Eq. (8) and noting that $\frac{s_0}{s_y} = \frac{s_0}{s_x}$ [30], we have

$$s_{xy}^o = \frac{e\hbar}{2mV} \sum_n \sum_{\mathbf{k}} \frac{f_{n\mathbf{k}}}{\kappa_{n\mathbf{k}}} [\kappa_{n\mathbf{k}} \cdot \mathbf{A}]_y; \quad (19)$$

where $\kappa_{n\mathbf{k}}$ is defined as $\kappa_{n\mathbf{k}} = (E_{n\mathbf{k}} - E_{n^0\mathbf{k}})/\hbar$. Similarly, we also obtain,

$$\sigma_{xy}^o = \frac{e\hbar}{mV} \sum_n \sum_{\mathbf{k}} \frac{f_{n\mathbf{k}}}{\kappa_{n\mathbf{k}}} [\kappa_{n\mathbf{k}} \cdot \mathbf{A}]_y^2; \quad (20)$$

where $\sigma_{xy}^0 = \sigma_{yx}^0$ was used [30]. The spin Hall and OAM Hall conductivities are therefore related to Berry vector potential. The Berry curvature is $(\mathbf{k})_z = [\mathbf{r}_k \cdot \mathbf{A}_k] = \frac{(\frac{2}{j^2} - \frac{2}{j})}{2} (2) (\mathbf{k})$. The corresponding Berry phase is then given by the path integral of the Berry vector potential, i.e., $\theta = \oint_C d\mathbf{l} \cdot \mathbf{A} = \oint_R (\mathbf{k})_z dk_x dk_y = \frac{(\frac{2}{j^2} - \frac{2}{j})}{2} = \text{sign}(\frac{2}{j^2} - \frac{2}{j})$, where R is the region containing the origin in the \mathbf{k} -plane. The Berry curvature z is zero for $k \neq 0$ but non-zero for $k = 0$ where the two bands of the Rashba-Dresselhaus system are degenerate. As for the spin transverse force for the Luttinger Hamiltonian given in Ref. 29, the corresponding spin transverse force in Rashba-Dresselhaus system can also be given in terms of the Berry curvature. Even though the Berry curvature vanishes for $k \neq 0$, the spin Hall current can nonetheless occur due to the Aharonov-Bohm-like effect at $k = 0$ [1].

Let us now discuss the effects of the different choice of the eigenstates on the above findings. In, e.g., Ref. [2], the eigenstates ($j^f k i$)

$$|j^f k i\rangle = \frac{1}{\sqrt{2}} \begin{pmatrix} ie^i \\ 1 \end{pmatrix}; |j^f k i\rangle = \frac{1}{\sqrt{2}} \begin{pmatrix} 1 \\ ie^i \end{pmatrix} : (21)$$

were used for the Rashba-Dresselhaus system. We find that the unitary transformation defined by the matrix

$$U = \frac{1}{2} \begin{pmatrix} 1+e^i & i-e^i \\ e^i & ie^{2i} \end{pmatrix} \begin{pmatrix} i-e^i \\ 1+e^i \end{pmatrix} (22)$$

with $UU^\dagger = U^\dagger U = 1$, will transform the eigenstates of Eq. (5) to that of Eq. (21), i.e., $|j^f k i\rangle = U |j k i\rangle$. Using the eigenstates in Eq. (21), the Berry vector potential is given by

$$\begin{aligned} A_+ &= \hbar^f k j(i) \frac{\partial}{\partial k} |j^f k i\rangle = \frac{1}{2} \frac{\partial}{\partial k} \\ A_- &= \hbar^f k j(i) \frac{\partial}{\partial k} |j^f k i\rangle = + \frac{1}{2} \frac{\partial}{\partial k} \end{aligned} (23)$$

that depends on the band index n . We may define $A_n = nA$ for both the bases of (5) and (21). As a result, the Berry phase given by Eq. (16) also depends on the band index n [32], i.e.,

$$\theta = \oint_C A_n(\mathbf{k}) d\mathbf{l} = \text{sign}(\frac{2}{j^2} - \frac{2}{j}) = \text{sign}(\frac{2}{j^2} - \frac{2}{j}); (24)$$

where θ is the Berry phase when the basis of Eq. (5) is used. In contrast, the signs of the Berry phase for the two bands are the same in the choice of the eigenstates of Eq. (5). Nevertheless, we can write $\theta_n = \theta$ with $n = \pm 1$. Note that the charge Hall effect would be zero when the basis of Eq. (21) is used, and would be non-zero if the basis of Eq. (5) is chosen, as have been pointed out in Ref. 32.

Using $A = \frac{1}{2} \frac{\partial}{\partial k}$ (Eq. 18), we can show that $A = [\mathbf{k} \cdot \mathbf{A}_k] a_0$, where $a_0 = (\frac{k_y}{k^2}, \frac{k_x}{k^2}) = \frac{\mathbf{e}}{k}$ and $[\mathbf{k} \cdot \mathbf{A}_k] = (\frac{2}{j^2} - \frac{2}{j}) = 2 \cdot \frac{1}{j} \cdot \frac{1}{j} = \frac{2}{j^2}$ which depends only on j . After some

vector algebra calculations, the spin Hall conductivity in Eq. (19) can be written as

$$\sigma_{xy}^0 = \frac{e}{8} \frac{X}{2} \oint_C d\mathbf{l} \cdot n[\mathbf{k} \cdot \mathbf{A}_k] a_0 \frac{k_F^n}{k_F^+ - k_F^-}; (25)$$

where $(k_F^+ - k_F^-) = \frac{2m}{\hbar^2} \frac{(\cdot)}{2}$ was used. Because $(k_F^n - k_F^+) = n(k_F^+ - k_F^-)$, Eq. (25) becomes

$$\sigma_{xy}^0 = \frac{e}{16} \frac{X}{2} \oint_C d\mathbf{l} \cdot n[\mathbf{k} \cdot \mathbf{A}_k] a_0 (26)$$

where $A_n = nA$ with $n = \pm 1$. Using the definition of Berry phase in Eq. (16), the spin Hall conductivity can be written as

$$\sigma_{xy}^0 = \frac{e}{16} \frac{X}{2} \oint_C d\mathbf{l} \cdot (nA_n) = \frac{e}{16} \frac{X}{2} n_n; (27)$$

where $n_n = n$ with $n = \pm 1$, in agreement with Ref. 23. In other words, the spin Hall conductivity can be written as a line integral of the Berry vector potential or a surface integral of the Berry curvature. Note that Eq. (27) holds irrespective of the choice of the eigenstates.

For the OAM Hall conductivity, similarly, Eq. (20) can be rewritten as

$$\sigma_{xy}^0 = \frac{e}{8} \frac{X}{2} \oint_C d\mathbf{l} \cdot [\mathbf{k} \cdot \mathbf{A}_k] a_0; (28)$$

This expression has also been given in Ref. 33, where $[\mathbf{k} \cdot \mathbf{A}_k] = \sim (\frac{2}{j^2} - \frac{2}{j}) = 2 \cdot \frac{1}{j} \cdot \frac{1}{j} = \frac{2}{j^2}$ was regarded as the OAM of the eigenstates in the absence of any applied electric field. We believe that this interpretation is inappropriate because the expectation value of the conventional OAM operator depends on the choice of bases, as will be shown in next Subsec. below. In next Subsec., we also argue that before an electric field is applied, the OAM of the eigenstates is zero. Finally, we also find that the ratio of the spin to OAM Hall conductivity is

$$\frac{\sigma_{xy}^0}{\sigma_{xy}^0} = 2[\mathbf{k} \cdot \mathbf{A}_k] j = m \quad \text{where } m \text{ is an integer.}$$

E. Origin of the orbital angular momentum Hall current

All electrons have an intrinsic spin of $\frac{1}{2}$. Before an in-plane electric field is applied, the spins of the electrons are all aligned in the xy -plane, as shown in Fig. 1(a)-(b). When an in-plane electric field is applied, the SO coupling gives rise to not only a spin transverse force on a moving electron [34, 35] but also an effective SO magnetic torque. The Rashba-Dresselhaus Hamiltonian can be written as $(H_R(\mathbf{k}) + H_D(\mathbf{k})) = \sim B_{eff} \cdot \mathbf{e}_z$ where $B_{eff} = (\hbar k_x \hat{e}_z) \cdot (\hbar k_x \hat{e}_x + \hbar k_y \hat{e}_y)$ is the effective SO magnetic field. The dynamics of the z component of spin can be derived from the Heisenberg equation of motion and we obtain $d_z(t)/dt = \frac{1}{i\hbar} [z, \frac{p^2}{2m} + H_D + H_R + eE_y] =$

$\frac{1}{i\hbar} [z; H_D + H_R] = \frac{1}{i\hbar} [z; i] B_{eff}^i$. Using the commutation relation of spin matrix $[i; j] = 2i \epsilon_{ijk} k_k$, we have $(ds_z(t)/dt) = \frac{2}{\hbar} (s(t) \cdot B_{eff})_z$, where $s = \frac{\hbar}{2} \sigma$. From the equation of motion of electron in k -space, we also have $k_y(t) - k_y(t_0) = \frac{eE}{\hbar} t_0$ and $k_x = 0$. Therefore, after a short time t_0 , the Fermi surface (i.e., the circle for $n = 1$) would move along $-k_y$ direction with the distance $eEt_0 = \hbar$. This implies that the variation of the effective SO magnetic field is $B_{eff} = (\hat{e}_x + \hat{e}_y) k_y$. Consequently, each spin feels the effective SO magnetic torque $s(0) \cdot B_{eff}$ and tilts out of the xy plane. The quantum dynamical analysis of spin for the Rashba-Dresselhaus system has been given in [23]. Here we use the quantum perturbation method to evaluate the response quantities.

Let us expand the wave function to first order of electric field, $|jki\rangle = |jki\rangle + |jki^{(1)}\rangle$ where the perturbed wave function is

$$|jki^{(1)}\rangle = eE \sum_{n^0(n^0 \neq n)} \frac{\langle n^0 k | j | 0 \rangle k_y |jki\rangle}{E_{nk} - E_{n^0k}} |jki\rangle. \quad (29)$$

The expectation value of the z component of spin can be evaluated by $\langle n^0 k | j_z | jki \rangle^0 = \hbar s_{zi_0} + \hbar s_{zi}$ where $\hbar s_{zi_0} = \langle n^0 k | j_z | jki \rangle = 0$ and the z component of the spin in first order of electric field is given by $\hbar s_{zi} = 2 \text{Re} \langle n^0 k | j_z | jki^{(1)} \rangle = eE \sim (\frac{\hbar}{2})^2 \cos^2 = 4nk^2 \sin^2(\frac{\pi}{4})$. Therefore, for $k_x > 0$, the spins on the outer (inner) sheet tend to tilt down (up) and for $k_x < 0$, the spins on the outer (inner) sheet tend to tilt up (down), as shown in the right panel of Fig. 1(b). This results in transverse spin Hall currents with spin polarization in the z direction.

Now consider the OAM $L_z = \hbar(x \cdot k)_z$. The expectation value $\langle n^0 k | j_z | jki \rangle^0 = \hbar L_{zi_0} + \hbar L_{zi}$ where $\hbar L_{zi_0} = \langle n^0 k | j_z | jki \rangle$ and $\hbar L_{zi} = 2 \text{Re} \langle n^0 k | j_z | jki^{(1)} \rangle$. In contrast to the spin case, before an electric field is applied, as argued below, all the eigenstates carry zero orbital angular momentum, i.e., $\hbar L_{zi_0} = 0$, as illustrated in the left panel of Fig. 1(c). In the absence of the applied electric field, the diagonal matrix elements of the OAM depend on the choice of the eigenstates, though the off-diagonal matrix elements of the OAM do not. For example, if we choose the eigenstates of Eq. (5), together with the conventional position operator $x = i\hbar k$, $\hbar L_{zi_0} = \langle n^0 k | j_z | jki \rangle = \hbar(x \cdot k)_z = \hbar(x \cdot k)_z = 2\hbar^2 \sin^2(\frac{\pi}{4})$, a value which has also been obtained in Ref. 33. On the other hand, if we use the eigenstates $|jki\rangle = \frac{1}{\sqrt{2}} e^{i(k \cdot r)} |jki\rangle$, $\hbar L_{zi_0} = 0$. This is of course unsatisfactory, and therefore, we propose to define a gauge invariant position operator $X = i\hbar k + A(k)$ to resolve the problem (see Appendix D). We can show that with this gauge invariant position operator X , $\hbar L_{zi_0} = 0$, irrespective of the choice of the phase factor of the eigenstates. Therefore, we believe that all the eigenstates of the Rashba-Dresselhaus system carry zero OAM in the absence of applied electric fields. Importantly, the other quantities such as $\hbar s_{zi}$

and $\hbar L_{zi}$, which contain only the $n \in n^0$ matrix elements, are independent of the choice of the phase factor and also the choice of the position operator.

As an in-plane electric field is applied, the dynamics of the z -component of the OAM can be obtained by means of Heisenberg equation of motion: $dL_z(t)/dt = \frac{d}{dt} \langle X \cdot k \rangle_z = \frac{2}{\hbar} (s(t) \cdot B_{eff}^0)_z + (x \cdot F)_z$ where $B_{eff}^0 = B_{eff} \cdot j$ and $F = -eE = -eE \hat{e}_y$. The second term $(x \cdot F)_z = -x \cdot k$ is the classical external torque which causes the orbital motion of the electrons and depends on the choice of the origin of the coordinate system. The first term $\frac{2}{\hbar} (s \cdot B_{eff}^0)_z$ is the effective SO magnetic torque. If we use the gauge invariant position operator, the classical torque $(x \cdot F)_z$ does not contribute to the variation of the OAM in a short time t_0 . We can show that $\frac{d}{dt} \langle X \cdot k \rangle_z = \frac{2}{\hbar} (s(t) \cdot B_{eff}^0)_z - X(t) \cdot E + k_y z$, where $z = r_k \cdot A^{(2)}(k)$ and is zero because $k \cdot A = 0$. After a short time t_0 , $\hbar X(0) \cdot k_y$ vanishes because $\hbar X(0) \cdot i = 0$ and the z component of the OAM for each eigenstate is induced by the effective SO magnetic torque and external torque only. In our calculations, we treat the potential $eE y$ as a perturbation and use again the quantum perturbation method instead of solving the Heisenberg equation of motion. We find that the z component of the OAM is $\hbar L_{zi} = eE \sim (\frac{\hbar}{2})^2 \cos^2 = 4nk^2 \sin^2(\frac{\pi}{4}) = \hbar s_{zi} [(\frac{\hbar}{2})^2 \cos^2 = 2(\frac{\hbar}{2})^2]$, as illustrated in the right panel of Fig. 1(c). Therefore, under the in-plane electric field along the y axis, the electrons on the outer (inner) sheet with $k_x > 0$ drift toward the x axis, carrying the downward (upward) tilted spinors as well as finite positive (negative) OAM $\hbar L_{zi}$, and the electrons on the outer (inner) sheet with $k_x < 0$ drift toward the x axis, carrying the upward (downward) tilted spinors as well as finite negative (positive) OAM $\hbar L_{zi}$. This gives rise to the OAM Hall current. It is interesting to note that in the pure Rashba system ($\alpha = 0$ and $(\frac{\hbar}{2})^2 \cos^2 = 2(\frac{\hbar}{2})^2 = 1$), the $\hbar s_{zi}$ and $\hbar L_{zi}$ have the same magnitude but the opposite signs and hence cancel each other exactly. This is due to the fact that the z -component of the total angular momentum is conserved in pure Rashba system.

III. SYSTEMS WITH BOTH RASHBA AND DRESSELHAUS SPIN-ORBIT COUPLINGS

The calculated total and decomposed spin and OAM Hall conductivities are summarized in Table I. The total spin and OAM Hall conductivities are displayed as a function of the ratio $j = j_0$ in Fig. 2. The total angular momentum Hall conductivity ($\frac{s_0}{x_y} + \frac{s}{x_y} + \frac{o_0}{x_y} + \frac{o}{x_y}$) is (see Table I)

$$\left(\frac{2}{j^2} \frac{e}{2} \right); \quad \frac{2}{2} \neq \frac{2}{2} \quad (30)$$

It is clear that in 2DEG systems with the Rashba-Dresselhaus SO coupling, the total angular momentum

TABLE I: Total and decomposed spin (a) and orbital angular momentum (b) Hall conductivities of a two-dimensional electron system with Rashba-Dresselhaus spin-orbit coupling.

(a) Spin Hall conductivity			
	$\lambda^2 > \beta^2$	$\lambda^2 = \beta^2$	$\lambda^2 < \beta^2$
σ_{xy}^s	$\frac{e}{8}$	0	$\frac{e}{8}$
σ_{xy}^o	$\frac{e}{4}$	0	$\frac{e}{4}$
σ_{xy}	$\frac{3e}{8}$	0	$\frac{5e}{8}$

(b) OAM Hall conductivity			
	$\lambda^2 > \beta^2$	$\lambda^2 = \beta^2$	$\lambda^2 < \beta^2$
σ_{xy}^o	$\frac{2 + \sqrt{2}}{j^2 - 2} \frac{e}{8}$	0	$\frac{2 + \sqrt{2}}{j^2 - 2} \frac{e}{8}$
σ_{xy}^s	$\frac{2 + \sqrt{2}}{j^2 - 2} \frac{e}{4}$	0	$\frac{2 + \sqrt{2}}{j^2 - 2} \frac{e}{4}$
σ_{xy}	$\frac{2 + \sqrt{2}}{j^2 - 2} \frac{e}{8}$	0	$\frac{2 + \sqrt{2}}{j^2 - 2} \frac{e}{8}$

Hall conductivity is in general not zero, except that $\lambda^2 = \beta^2$ or $j = 0$ (pure Rashba SO coupling). The sign of the total angular momentum Hall conductivity is always negative, and, as will be discussed shortly, this is because the Hall conductivity is dominated by the negative OAM Hall conductivity. Furthermore, when the two SO coupling strengths are comparable, the total angular momentum Hall conductivity is very large, suggesting the interesting possibility of tuning the angular momentum Hall effect by varying the Rashba SO coupling strength. This large total Hall conductivity results from the large OAM Hall conductivity in both the conventional and present definitions of spin current (see Table I). The conventional OAM Hall conductivity is the same as that given in Ref. 33. This singularly large OAM conductivity in the region that $j = j$ approaches to unity, could lead to spontaneous magnetization, as suggested in Ref. 33. Nevertheless, we believe that this singular behavior of the OAM conductivity near $j = 1$ is unphysical and is perhaps due to the neglect of the disorder in the present calculations. The disorder due to, e.g., in purity scattering and electron-electron interaction is known to have pronounced effects on the spin Hall effect [9, 10, 11]. The infinite large OAM conductivity is expected to be suppressed by the disorder effects in real 2DEG systems. Nonetheless, further calculations taking into the disorder effects are beyond the scope of the present paper.

Shen [23] recently pointed out that in the 2DEG systems with both Rashba and Dresselhaus couplings, the spin current along the z direction is antisymmetric with respect to a unitary transformation: $\sigma_x \rightarrow -\sigma_x$; $\sigma_y \rightarrow \sigma_y$; $\sigma_z \rightarrow \sigma_z$. This antisymmetry makes the conventional spin Hall conductivity changes sign at $\lambda^2 = \beta^2$. It is interesting to note that the spin torque Hall conductivity and hence the total spin Hall conductivity also change sign at $\lambda^2 = \beta^2$ when one moves from the region where Dresselhaus coupling dominates to the region where Rashba coupling dominates (Table I and Fig. 2). This shows that our calculated spin torque and total spin

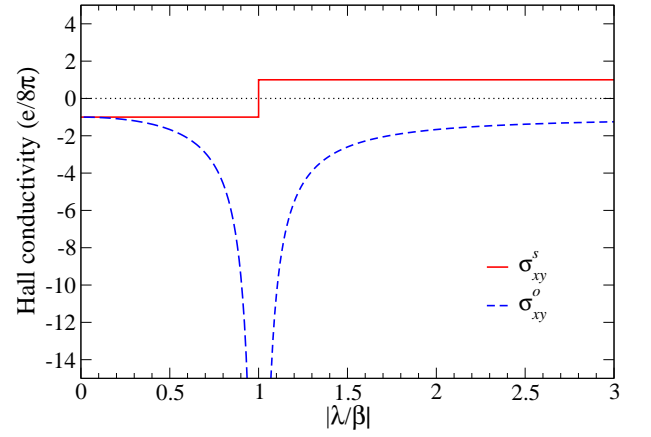


FIG. 2: (Color online) Spin (σ_{xy}^s , solid line) and orbital angular momentum (σ_{xy}^o , dashed line) Hall conductivities versus the strength ratio $j = j$ of the Rashba (λ) to Dresselhaus (β) spin-orbit coupling.

Hall conductivities also obey the requirement of this antisymmetry. We also note that as for the case of pure Rashba coupling [16], the spin torque Hall conductivity is twice as large as the conventional spin Hall conductivity but has an opposite sign (Table I), giving rise to the result that the conserved spin Hall conductivity has the same size but opposite sign to the conventional spin Hall conductivity.

On the other hand, all the (total, torque and conventional) OAM Hall conductivities do not change sign at $\lambda^2 = \beta^2$, as shown in Table I and Fig. 2. As for the case of spin Hall effect, the torque OAM Hall conductivity is twice as large as the conventional OAM Hall conductivity but has an opposite sign, resulting in that the effective OAM Hall conductivity has the same size but opposite sign to the conventional OAM Hall conductivity (Table I). The conventional OAM Hall conductivity has been reported in Ref. 33, and our result is consistent with this previous calculation.

IV. SYSTEMS WITH EITHER PURE RASHBA TERM OR PURE DRESSELHAUS TERM

A. Pure Rashba spin-orbit coupling

In the case of $\beta = 0$ and $\lambda \neq 0$, the Hamiltonian reduces to the pure Rashba Hamiltonian. The spin torque operator becomes

$$\hat{H}_s^R = \frac{1}{i} [\hat{s}_z; \frac{\hat{p}^2}{2m} + H_R]; \quad (31)$$

and the y -component of velocity operator is

$$v_y^R = \frac{p_y}{m} + \frac{\lambda}{\hbar} \sigma_x; \quad (32)$$

The torque correction term for the spin Hall conductivity is $e=4$, and for the OAM Hall conductivity is $e=4$, which exactly cancel each other. This result is confirmed by the relation $[L_z; H_R] = [S_z; H_R]$ that is present in the Rashba Hamiltonian. Including the torque correction term, we get an effective spin Hall conductivity of $e=8$, and an effective OAM Hall conductivity of $e=8$. This implies that when the torque correction term is taken into account, the spin Hall current is still exactly canceled by the accompanied OAM Hall current and there is no total angular momentum current in the pure Rashba system. This interesting observation has been reported before in Ref. 7 in the context of the conventional definition of the spin and OAM currents. This may be expected because $[S_z + L_z; H_R] = 0$ and the conservation of the total angular momentum therefore must be obeyed no matter what definitions of the effective angular momentum currents one adopts.

Nonetheless, we want to point out here that the spin Hall effect in the pure Rashba Hamiltonian can still manifest itself and be detected in several ways, even though the total angular momentum Hall current is zero. It is well known that the magnetic dipole moment associated with the spin of an electron is $s = 2s_B$ and the one associated with the OAM of an electron is $o = L_B$ (see, e.g., [36]). Consequently, although the total angular momentum $(s_z + L_z)$ current is zero, the total magnetization $[(\frac{z}{s} + \frac{z}{o}) = (2s_z + L_z)_B]$ current would not be zero and will give rise to finite magnetization at the edge of the sample. Therefore, the spin Hall effect in the pure Rashba Hamiltonian can in principle be probed in at least two ways. As noted in Ref. 7, one is by measuring the electric field induced by the nonzero magnetization current [37] and the other is the magnetization at the sample edges. Recently, it is suggested in Ref. 11 that spin current can be detected by measuring time dependent magnetization precession.

B. Pure Dresselhaus spin-orbit coupling

In the case of $\alpha = 0$ and $\beta \neq 0$, the Hamiltonian reduces to the pure Dresselhaus Hamiltonian. In this case, the total, torque correction and conventional spin and OAM Hall conductivities have the same signs (Table I). For example, the total spin Hall conductivity is $e=8$, being the same as the total OAM Hall conductivity, thereby giving rise to a total angular momentum Hall conductivity of $e=4$. In the Dresselhaus Hamiltonian, the total angular momentum is not conserved, i.e., $[S_z + L_z; H_D] = 2i(\alpha p_y + \beta p_x) \neq 0$. Instead, we find $[S_z; H_D] = [L_z; H_D]$ or $[S_z - L_z; H_D] = 0$. Therefore, the spin and OAM Hall conductivities would add up rather than cancel each other, in contrast to the Rashba Hamiltonian.

We notice that the spin Hall conductivity in the clean limit is constant in either pure Rashba system, or pure Dresselhaus system, or the mixture Rashba-Dresselhaus

system [see Table I(a)]. Interestingly, in Refs. 10 and 11, it is pointed that the constant spin Hall conductivity in pure Rashba system would result in an unphysically growth of the magnetization with time. This is due to the fact that the conventionally defined spin Hall current in the pure Rashba system turns out to be proportional to the time derivative of the magnetization of the system. This linear relation between the conventional spin Hall current and the time derivative of the magnetization should also exist in the pure Dresselhaus system because the two systems are related by the unitary transformation: $\psi_x \rightarrow \psi_y$ and $\psi_y \rightarrow \psi_x$, as mentioned above in Sec. III. Indeed, we find that the conventional spin current in the pure Dresselhaus system is $j_x^{sz} = \frac{\hbar}{4} f v_x$; $j_y^{sz} = \frac{\hbar}{2m} z p_x$, where the relation $f_i; j_g = 2 i_j$ was used. Furthermore, it can be shown that the spin precession and conventional spin current satisfy the relations: $\frac{dh_y(t)i}{dt} = \frac{2}{\hbar} \hbar p_x z i(t) = \frac{4m}{\hbar^3} \hbar j_x^{sz}(t)i$ and $\frac{dh_x(t)i}{dt} = \frac{4m}{\hbar^3} \hbar j_y^{sz}(t)i$. Therefore, the constant conventional spin current in the clean limit in the pure Dresselhaus system would also lead to the unphysical consequence that both $h_y(t)i$ and $h_x(t)i$ depend linearly on time, resulting in an infinite growth of the magnetization. In contrast, because the conserved spin current satisfies the continuity equation [Eq. (1)], we find no such relation that the conserved spin current is proportional to the time derivative of the spin operator, thereby, free from the artifact discussed above, as also pointed out in Ref. 38.

V. CONCLUSIONS

In conclusion, we have calculated the spin Hall conductivity in the Rashba-Dresselhaus Hamiltonian with the spin torque correction in the absence of disorder, and find it to have the same magnitude but an opposite sign to the result reported before [4, 23]. The spin Hall conductivity in the absence of disorder is still a constant in pure Dresselhaus (or Rashba) system even when the torque correction is considered. We also introduce the conserved effective OAM current and find that in general, the OAM Hall effect does not cancel the spin Hall effect in the 2DEG with the Rashba-Dresselhaus spin-orbit coupling. The OAM Hall conductivity depends significantly on the strength ratio of the Rashba to Dresselhaus spin-orbit coupling, suggesting that one can manipulate the total Hall current through tuning the Rashba coupling by a gate voltage [39, 40]. We argue that in a pure Rashba system, though the spin Hall conductivity is exactly cancelled by the OAM Hall conductivity due to the angular momentum conservation, the spin Hall effect still manifests itself as a nonzero magnetization Hall current and finite magnetization at the sample edges because the magnetic dipole moment associated with the spin of an electron is twice as large as that of the OAM. We show that the spin and OAM Hall conductivities have a simple relation to the Berry vector (or gauge) potential. We also

calculate the electric field-induced OAM and discuss the origin of the OAM Hall current.

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APPENDIX A: THE CONTINUITY EQUATION FOR THE EFFECTIVE SPIN CURRENT

In this appendix, we derive the continuity equation for the effective spin current. A similar derivation can also be found in [15]. The definition of spin density is $S_z = \frac{1}{2} s_z$, where $s_z = \frac{\hbar}{2} \sigma_z$. Using $i\hbar \frac{\partial}{\partial t} = H$ and $H = H_0 + eE_x x$, we obtain the following equation:

$$\begin{aligned} \frac{\partial}{\partial t} [\frac{1}{2} s_z] &= \frac{1}{i\hbar} (\frac{1}{2} s_z H_0 - (H_0) \frac{1}{2} s_z) \\ &= \frac{1}{i\hbar} f [\frac{1}{2} s_z \frac{p^2}{2m} - (\frac{p^2}{2m}) \frac{1}{2} s_z] \quad (A1) \\ &\quad + [\frac{1}{2} s_z H_R - (H_R) \frac{1}{2} s_z] \\ &\quad + [\frac{1}{2} s_z H_D - (H_D) \frac{1}{2} s_z] g; \end{aligned}$$

where we have used $[s_z; x] = 0$. First, we combine the following two equations:

$$\frac{\partial}{\partial x_i} (\frac{1}{2} s_z \frac{\partial}{\partial x_i} x) = (\frac{\partial}{\partial x_i} \frac{1}{2} s_z) \frac{\partial}{\partial x_i} x + \frac{1}{2} s_z \frac{\partial}{\partial x_i} \frac{\partial}{\partial x_i} x$$

$$\frac{\partial}{\partial x_i} (\frac{\partial}{\partial x_i} \frac{1}{2} s_z) = (\frac{\partial}{\partial x_i} \frac{\partial}{\partial x_i} \frac{1}{2} s_z) + \frac{\partial}{\partial x_i} (\frac{\partial}{\partial x_i} \frac{1}{2} s_z):$$

Using the definition of momentum operator $p = i\hbar \nabla$ and $(\frac{1}{2} s_z \frac{p^2}{2m})^y = (\frac{p^2}{2m})^y \frac{1}{2} s_z$, we obtain:

$$p^2 [2\text{Re}(\frac{1}{2} s_z)] = [\frac{1}{2} s_z p^2 - (p^2) \frac{1}{2} s_z]: \quad (A2)$$

Next, consider the term $[\frac{1}{2} s_z H_R - (H_R) \frac{1}{2} s_z]$ which contains only the Rashba Hamiltonian. We obtain the following equations:

$$\begin{aligned} [\frac{1}{2} s_z H_R - (H_R) \frac{1}{2} s_z] \\ = \frac{2i}{\hbar} \frac{1}{2} s_z p_{\sim} - \frac{1}{2} p_{\sim} [\frac{1}{2} s_z (\sim \hat{e}_z)] \quad (A3) \end{aligned}$$

and

$$\begin{aligned} [\frac{1}{2} s_z H_R - (H_R) \frac{1}{2} s_z] \\ = [\frac{1}{2} s_z H_R - (H_R) \frac{1}{2} s_z]^y \\ = \frac{2i}{\hbar} [\frac{1}{2} s_z p_{\sim} - \frac{1}{2} p_{\sim} [\frac{1}{2} s_z (\sim \hat{e}_z)]]^y: \quad (A4) \end{aligned}$$

We combine Eq. (A3) and Eq. (A4):

$$\begin{aligned} [\frac{1}{2} s_z H_R - (H_R) \frac{1}{2} s_z]^y \\ = \frac{2i}{\hbar} \text{Re}[\frac{1}{2} s_z (p_{\sim} - \frac{1}{2} p_{\sim} [\frac{1}{2} s_z (\sim \hat{e}_z)])^y]: \quad (A5) \end{aligned}$$

Now consider the term $[\frac{1}{2} s_z H_D - (H_D) \frac{1}{2} s_z]$ which contains only the Dresselhaus Hamiltonian. From the second term $(H_D) \frac{1}{2} s_z$, we obtain:

$$\begin{aligned} (H_D) \frac{1}{2} s_z &= \frac{1}{\hbar} [p_x \frac{1}{2} s_x + p_y \frac{1}{2} s_y] z \\ &= \frac{1}{\hbar} p_x (\frac{1}{2} s_x z) - \frac{1}{\hbar} \frac{1}{2} s_x p_x z \\ &\quad - \frac{1}{\hbar} p_y (\frac{1}{2} s_y z) + \frac{1}{\hbar} \frac{1}{2} s_y p_y z \\ &= \frac{1}{\hbar} f p_x (\frac{1}{2} s_z x) - p_y (\frac{1}{2} s_z y) g \\ &\quad - \frac{1}{\hbar} \frac{1}{2} (p_x x - p_y y) z: \quad (A6) \end{aligned}$$

and then:

$$\begin{aligned} [\frac{1}{2} s_z H_D - (H_D) \frac{1}{2} s_z]^y \\ = \frac{2i}{\hbar} \frac{1}{2} s_y (p_x y + p_y x) \\ + \frac{1}{\hbar} f p_x [\frac{1}{2} s_z x] - p_y [\frac{1}{2} s_z y] g \\ = \frac{2i}{\hbar} \text{Re}[\frac{1}{2} s_y (p_x y + p_y x)] \\ + \frac{1}{\hbar} f p_x \text{Re}[\frac{1}{2} s_z x] - p_y \text{Re}[\frac{1}{2} s_z y] g; \quad (A7) \end{aligned}$$

where we have used the relation: $[\frac{1}{2} s_z H_D - (H_D) \frac{1}{2} s_z]^y = [\frac{1}{2} s_z H_D - (H_D) \frac{1}{2} s_z]^y$. Substituting Eqs. (A2), (A5) and (A7) into (A1), we obtain

$$\begin{aligned} \frac{\partial}{\partial t} [\frac{1}{2} s_z] \\ = \frac{1}{\hbar} \text{Re}[\frac{1}{2} s_z (\frac{p^2}{m} - \frac{1}{2} \sim \hat{e}_z - \frac{1}{2} (x \hat{e}_x - y \hat{e}_y))] \\ + \frac{2}{\hbar} \text{Re}[\frac{1}{2} s_y (p_{\sim} - \frac{1}{2} p_{\sim} [\frac{1}{2} s_z (\sim \hat{e}_z)])^y] \\ + \frac{2}{\hbar} \text{Re}[\frac{1}{2} s_z (p_x y + p_y x)]^y: \quad (A8) \end{aligned}$$

Consider the commutator $[z; H_0]$, and we have

$$\frac{1}{i\hbar} [z; \frac{p^2}{2m} + H_R + H_D] = \frac{2}{\hbar} p_{\sim} + \frac{2}{\hbar} (p_x y + p_y x): \quad (A9)$$

The velocity operator in the Rashba-Dresselhaus system satisfy the following relation:

$$\begin{aligned} v &= \frac{1}{i\hbar} [x; H] = \frac{1}{i\hbar} [x; H_0] \\ &= \frac{p}{m} (\sim \hat{e}_z) - \frac{1}{\hbar} (x \hat{e}_x - y \hat{e}_y): \quad (A10) \end{aligned}$$

Finally, substituting Eq. (A 10) and Eq. (A 9) into Eq. (A 8), we obtain the continuity equation of the effective spin current

$$\frac{\partial}{\partial t} [\psi S_z] = -r \text{Re}[\psi f^z] + \text{Re}[\psi s_z]; \quad (\text{A } 11)$$

where we have used $s_z = \frac{1}{2} \psi z$, $f^z = \frac{1}{2} f v; s_z g$ and $s_z = \frac{1}{i\hbar} [S_z; H_0]$. With the definition of spin density $S_z = \psi S_z$, spin current $J_s = \text{Re}[\psi f^z]$ and spin torque $T_z^s = \text{Re}[\psi s_z]$, Eq. (A 11) can be rewritten as

$$\frac{\partial S_z}{\partial t} + r J_s = T_z^s \quad (\text{A } 12)$$

which is in agreement with Ref. 16.

APPENDIX B: THE CONTINUITY EQUATION FOR THE EFFECTIVE OAM CURRENT

In this appendix, we derive the continuity equation for the effective OAM current. Let us consider the z-component of the OAM density $L_z = \psi L_z$ and its partial time-derivative $i\hbar \frac{\partial}{\partial t} L_z$. Applying $i\hbar \frac{\partial}{\partial t} = H$ where $H = H_0 + eE \cdot x$, we have

$$\begin{aligned} i\hbar \frac{\partial}{\partial t} (\psi L_z) &= \psi L_z H_0 - (H_0) \psi L_z + \psi [L_z; eE \cdot x] \\ &= \psi L_z \left(\frac{p^2}{2m} + H_R + H_D \right) - \left(\frac{p^2}{2m} + H_R + H_D \right) \psi L_z \\ &\quad + \psi [L_z; eE \cdot x] \end{aligned} \quad (\text{B } 1)$$

First, using the commutation relations $[p; L_z] = i\hbar \hat{e}_z \cdot p$ and $[L_z; p^2] = 0$, we can show that:

$$\begin{aligned} i\hbar \psi L_z p^2 - (p^2 \psi) L_z g &= p \cdot [\psi p L_z - (p \cdot \psi) L_z g] \\ &= p \cdot [\psi f p; L_z g] - p^2 (\psi L_z) + p \cdot [\psi i\hbar \hat{e}_z \cdot p] \end{aligned} \quad (\text{B } 2)$$

For the Rashba Hamiltonian H_R , we have

$$\begin{aligned} (H_R) \psi L_z &= \frac{1}{\hbar} [p_y \psi x + p_x \psi y] L_z \\ &= \frac{1}{\hbar} p \cdot [\psi (\hat{e}_z \cdot L_z)] \\ &\quad + \frac{1}{\hbar} \psi (p_y x - p_x y) L_z \end{aligned}$$

and

$$\begin{aligned} i\hbar \psi L_z H_R - (H_R) \psi L_z g &= \psi [L_z; H_R] - \frac{1}{\hbar} p \cdot [\psi (\hat{e}_z \cdot L_z)] \end{aligned} \quad (\text{B } 3)$$

For the Dresselhaus Hamiltonian H_D , we obtain

$$\begin{aligned} i\hbar \psi L_z H_D - (H_D) \psi L_z g &= \psi [L_z; H_D] - \frac{1}{\hbar} p \cdot [\psi (\hat{e}_x \cdot L_z - \hat{e}_y \cdot L_z)] \end{aligned} \quad (\text{B } 4)$$

Substituting Eqs. (B 2), (B 3) and (B 4) into Eq. (B 1), we have

$$\begin{aligned} i\hbar \frac{\partial}{\partial t} (\psi L_z) &= p \cdot [\psi f \frac{p}{2m}; L_z g] + \psi [L_z; eE \cdot x] \\ &\quad - \frac{1}{\hbar} \psi (\hat{e}_z \cdot L_z) L_z - \frac{1}{\hbar} \psi (\hat{e}_x \cdot L_z - \hat{e}_y \cdot L_z) L_z \\ &\quad + \psi [L_z; H_R + H_D] - \frac{1}{2m} p^2 (\psi L_z) \\ &\quad + \frac{1}{2m} p \cdot [\psi i\hbar \hat{e}_z \cdot p] \end{aligned} \quad (\text{B } 5)$$

Putting Eq. (A 10) into Eq. (B 5), we have

$$\begin{aligned} \frac{\partial}{\partial t} (\psi L_z) &= -r \cdot [\psi \frac{1}{2} f v; L_z g] + \psi \frac{1}{i\hbar} [L_z; eE \cdot x] \\ &\quad + \psi \frac{1}{i\hbar} [L_z; H_0] - \frac{i\hbar}{2m} r^2 (\psi L_z) - p \cdot [\psi \hat{e}_z \cdot p] \end{aligned}$$

Finally, it can be shown that $p \cdot [\psi \hat{e}_z \cdot p]$ is purely imaginary, and $\psi L_z = \text{Re}(\psi L_z)$ is real for both the eigenstates of the Rashba-Dresselhaus Hamiltonian and the Bloch states ψ_k . The L_z continuity equation becomes:

$$\frac{\partial}{\partial t} (\psi L_z) = -r \text{Re}[\psi f^0] + \text{Re}[\psi \cdot] + \text{Re}[\psi \cdot E] \quad (\text{B } 6)$$

where $f^0 = \frac{1}{2} f v; L_z g$, $\cdot = \frac{1}{i\hbar} [L_z; H_0]$ and $\cdot E = \frac{1}{i\hbar} [L_z; eE \cdot x]$. With the OAM current density $J = \text{Re}[\psi f^0]$, the OAM torque density $T_z^o = \text{Re}[\psi \cdot]$ and the classical torque density $T_z^E = \text{Re}[\psi \cdot E]$, Eq. (B 6) can be rewritten as

$$\frac{\partial L_z}{\partial t} + r J = T_z^o + T_z^E; \quad (\text{B } 7)$$

which is the OAM continuity equation.

The torque $T_z^E = \text{Re}[\psi \cdot E]$ has a classical analogue. It can be regarded as the rotational torque moment due to the force eE exerted on a particle located at the position x with respect to the origin of the coordinate system. This can be seen from the commutator $[L_z; eE \cdot x] = i\hbar e(x \cdot E)$, and

$$T_z^E = \text{Re}[(\psi x) \cdot eE] \quad (\text{B } 8)$$

From the space integral $\int dV T_z^E = \text{Re}[\int dV (\psi x) \cdot eE]$, we obtain $\int dV T_z^E = \text{Re}[\hbar \langle j \rangle \cdot (eE)]$, where $\int dV x = \hbar \langle j \rangle$. Expanding the $\hbar \langle j \rangle$ in powers of electric field, we have $\hbar \langle j \rangle = \hbar_0 \langle j \rangle_0 +$

$\hbar \mathbf{x} \mathbf{i}^{(1)} + o(E^2)$, where j_0 satisfies the unperturbed wave equation $i\hbar \frac{\partial}{\partial t} j_0 = H_0 j_0$. Therefore, we obtain $\frac{d}{dt} T_z^E = \text{Re}[\langle j_0 | \hat{J}_z | j_0 \rangle] (eE)^2 + o(E^2)$. However, we should demand that the expectation value of the OAM in the unperturbed system is zero. This would imply that the expectation value of the position operator must be zero in the absence of the external electric field, as discussed in Appendix D. Finally, we obtain that the OAM continuity equation

$$\frac{\partial L_z}{\partial t} + \nabla \cdot \mathbf{J} = T_z^O \quad (\text{B } 9)$$

which is valid in first order of the electric field.

APPENDIX C: SPIN AND OAM TORQUE HALL CONDUCTIVITY

In this appendix, we derive the spin and orbital angular momentum (OAM) torque Hall conductivities (κ_{xy}) in the Rashba-Dresselhaus system. The conductivity in pure Rashba system can be obtained by setting $\beta = 0$ in the $\beta^2 > \alpha^2$ condition. The total torque conductivity is given by

$$\kappa_{xy} = (\kappa_{xy}^s + \kappa_{xy}^o) = \text{Re}[\langle j | \hat{J}_y(q) = \langle j | \hat{J}_y | j \rangle] \quad (\text{C } 1)$$

where $J_y(q)$ is defined as

$$J_y(q) = \frac{ie\hbar}{V} \sum_{n \in n^0} \sum_{\mathbf{k}} [\langle f_{n\mathbf{k}} | \langle f_{n^0\mathbf{k}+q} | \frac{\hbar \mathbf{k} \mathbf{j}(\mathbf{k}; q) j_0^0 \mathbf{k} + q i \hbar n^0 \mathbf{k} + q j \mathbf{v}(\mathbf{k}; q) j \mathbf{k} \mathbf{i}}{(E_{n\mathbf{k}} - E_{n^0\mathbf{k}+q})^2} \rangle, \quad (\text{C } 2)$$

where $\mathbf{k}(q) = \frac{1}{2}[\mathbf{k} + (\mathbf{k} + q)]$, $\mathbf{v}(\mathbf{k}; q) = \frac{1}{2}[\mathbf{v}(\mathbf{k}) + \mathbf{v}(\mathbf{k} + q)]$ and $\hat{J}_z = \frac{1}{i\hbar}[\mathbf{S}_z + \mathbf{L}_z; H_0]$ is the total torque. The equation (C1) suggests that we can choose $q = (\alpha_x; 0; 0)$ for simplicity. By the choice of $q = (\alpha_x; 0; 0)$, the $J_y(q)$ can be expanded in power of α_x , i.e., $J_y(q) = J_y^{(0)} + J_y^{(1)}\alpha_x + J_y^{(2)}\alpha_x^2 + o(\alpha_x^3)$, and the torque conductivity will be rewritten as: $\kappa_{xy} = \text{Re}[\langle j | J_y^{(1)} \rangle] = \text{Im}[\langle j | J_y^{(1)} \rangle]$ by using Eq. (C1).

To evaluate J_y in Eq. (C2), we first expand the matrix elements $\langle \mathbf{k} \mathbf{j}(\mathbf{k}; q) j_0^0 \mathbf{k} + q i \hbar n^0 \mathbf{k} + q j \mathbf{v}(\mathbf{k}; q) j \mathbf{k} \mathbf{i}$ to first

order of α_x :

$$\begin{aligned} & \langle \mathbf{k} \mathbf{j}(\mathbf{k}; q) j_0^0 \mathbf{k} + q i \hbar n^0 \mathbf{k} + q j \mathbf{v}(\mathbf{k}; q) j \mathbf{k} \mathbf{i} \\ &= \frac{n}{m} \frac{\partial}{\partial k_x} (k_x \sin \theta + k_y \cos \theta) \alpha_x \\ & \quad - \frac{1}{m} [k_y + k_y \cos(2\theta) + k_x \sin(2\theta)] \\ & \quad + \alpha_x \frac{\partial}{\partial k_x} (k_x \cos(2\theta) - k_y \sin(2\theta)) + \frac{\alpha_x}{2} \sin(2\theta) \\ & \quad - \frac{1}{m} [k_x + k_y \sin(2\theta) - k_x \cos(2\theta)] \\ & \quad + \alpha_x \frac{\partial}{\partial k_x} (k_y \cos(2\theta) + k_x \sin(2\theta)) \\ & \quad + \frac{\alpha_x}{2} (1 - \cos(2\theta)) + o(\alpha_x^2): \end{aligned} \quad (\text{C } 3)$$

We also need to expand the $(f_{n\mathbf{k}} - f_{n^0\mathbf{k}+q}) = (E_{n\mathbf{k}} - E_{n^0\mathbf{k}+q})^2$ to first order of q . We have

$$\begin{aligned} \frac{f_{n\mathbf{k}} - f_{n^0\mathbf{k}+q}}{(E_{n\mathbf{k}} - E_{n^0\mathbf{k}+q})^2} &= \frac{f_{n\mathbf{k}} - f_{n^0\mathbf{k}}}{(E_{n\mathbf{k}} - E_{n^0\mathbf{k}})^2} \\ & \quad + \alpha_x \frac{\partial}{\partial k_x} \left[\frac{f_{n\mathbf{k}} - f_{n^0\mathbf{k}}}{(E_{n\mathbf{k}} - E_{n^0\mathbf{k}})^3} \right] \\ & \quad + \frac{\partial f_{n^0\mathbf{k}}}{\partial E_{n^0\mathbf{k}}} \frac{\partial E_{n^0\mathbf{k}}}{\partial k_x} \frac{1}{(E_{n\mathbf{k}} - E_{n^0\mathbf{k}})^2} + o(\alpha_x^2): \end{aligned} \quad (\text{C } 4)$$

Assuming the Fermi energy is larger than the spin-orbit splitting and using $(k_F^+ - k_F^-) = 2m^* \beta \hbar^{-1}$ and $\kappa_{xy} = \text{Im}[\langle j | J_y^{(1)} \rangle]$, we can write the torque conductivity as

$$\begin{aligned} \kappa_{xy} &= \frac{e}{4} \frac{1}{(2\pi)^2} \int d\mathbf{k} \frac{G(\mathbf{k}; \mathbf{k}; \mathbf{k})}{(\mathbf{k} \cdot \mathbf{k})^3} \\ & \quad + \frac{e}{8} \frac{1}{(2\pi)^2} \int d\mathbf{k} \frac{H(\mathbf{k}; \mathbf{k}; \mathbf{k}) \cos \theta}{(\mathbf{k} \cdot \mathbf{k})^3}, \end{aligned} \quad (\text{C } 5)$$

where $G(\mathbf{k}; \mathbf{k}; \mathbf{k})$ and $H(\mathbf{k}; \mathbf{k}; \mathbf{k})$ are given by

$$\begin{aligned} G(\mathbf{k}; \mathbf{k}; \mathbf{k}) &= \frac{(\alpha^2 - \beta^2) \sin^2(\theta) \sin(2\theta)}{(\mathbf{k} \cdot \mathbf{k})^3} \\ H(\mathbf{k}; \mathbf{k}; \mathbf{k}) &= \sin \theta + \cos \theta \\ & \quad + (\alpha^2 - \beta^2) \frac{(\sin \theta \cos \theta) \cos(2\theta)}{(\mathbf{k} \cdot \mathbf{k})^2} \\ & \quad + (\alpha^2 + \beta^2) \frac{(\cos \theta + \sin \theta) \sin(2\theta)}{(\mathbf{k} \cdot \mathbf{k})^2} \\ & \quad + 2 \frac{(\cos \theta + \sin \theta)}{(\mathbf{k} \cdot \mathbf{k})^2}: \end{aligned}$$

Using $[\langle \mathbf{k} \cdot \mathbf{k} \rangle]^2 = (\alpha^2 + \beta^2)^2 \sin^2(2\theta)$, we find that $\frac{G(\mathbf{k})}{(\mathbf{k} \cdot \mathbf{k})^3} - \frac{H(\mathbf{k}) \cos \theta}{2(\mathbf{k} \cdot \mathbf{k})^2}$ can be written as:

$$\left[\frac{G(\mathbf{k}; \mathbf{k}; \mathbf{k})}{(\mathbf{k} \cdot \mathbf{k})^3} - \frac{1}{2} \frac{H(\mathbf{k}; \mathbf{k}; \mathbf{k})}{(\mathbf{k} \cdot \mathbf{k})^2} \right] = (\alpha^2 - \beta^2)^2 \frac{\sin \theta \cos \theta}{(\mathbf{k} \cdot \mathbf{k})^4} \quad (\text{C } 6)$$

From the above formula, we can easily check that Eq. (C6) is zero when we set $\alpha = 0$. From Eq. (C6), it follows that the torque conductivity vanishes in pure Rashba system (i.e. $\alpha = 0$) because the integral $\int_0^{2\pi} \sin \cos d\theta$ is zero. Our next step is to work out the integrals by using Residue method [41]. The crucial integrals are the followings ($j > j$):

$$\begin{aligned} \int_0^{2\pi} d\theta \frac{1}{[\alpha(\theta)]^2} &= \frac{2(\alpha^2 + \beta^2)}{(\alpha^2 - \beta^2)^3} \\ \int_0^{2\pi} d\theta \frac{\sin \cos}{[\alpha(\theta)]^2} &= \frac{2}{(\alpha^2 - \beta^2)^3} \end{aligned} \quad (C7)$$

For $j > j$, we can exchange the Rashba and Dresselhaus couplings in the integrals. Substituting Eq. (C6) and Eq. (C7) into Eq. (C5), we obtain the torque conductivity:

$$\kappa_{xy} = \frac{e}{2} \frac{\alpha^2}{j^2 - \beta^2 j} \quad (C8)$$

Since the commutation relation $[S_z + L_z; \frac{p^2}{2m} + H_R] = 0$, the Rashba coupling disappears in numerator of κ_{xy} . For $\frac{R}{S} = \frac{1}{i\alpha} [S_z; H_R(k)] = (\alpha k_x + \beta k_y)$, we can use the same steps as the calculation of κ_{xy} . The new $H_s(\alpha; \beta)$ and $G_s(\alpha; \beta)$ can be obtained by changing the α and β in $H(\alpha; \beta)$ and $G(\alpha; \beta)$. We have

$$\begin{aligned} \kappa_{xy}^R &= \kappa_{xy}^O \\ &= \frac{e}{8\alpha^2} \int_0^{2\pi} d\theta \frac{G_s(\alpha; \beta)}{[\alpha(\theta)]^2} \\ &\quad + \frac{e}{16\alpha^2} \int_0^{2\pi} d\theta \frac{H_s(\alpha; \beta) \cos}{[\alpha(\theta)]^2} \\ &= \frac{e}{8\alpha^2} \int_0^{2\pi} d\theta \frac{G(\beta; \alpha)}{[\alpha(\theta)]^2} \\ &\quad + \frac{e}{16\alpha^2} \int_0^{2\pi} d\theta \frac{H(\beta; \alpha) \cos}{[\alpha(\theta)]^2} \\ &= \frac{e}{4} \frac{\alpha^2}{j^2 - \beta^2 j} \end{aligned} \quad (C9)$$

Therefore, the spin torque Hall conductivity is

$$\begin{aligned} \kappa_{xy}^s &= \left(\frac{e}{4} \frac{\alpha^2}{j^2 - \beta^2 j} + \frac{e}{4} \frac{\beta^2}{j^2 - \alpha^2 j} \right) \\ &= \frac{e}{4} \frac{\alpha^2 + \beta^2}{j^2 - \beta^2 j} = \text{sign}(\alpha^2 - \beta^2) \frac{e}{4} \end{aligned} \quad (C10)$$

and the OAM torque Hall conductivity is

$$\begin{aligned} \kappa_{xy}^o &= \left(\frac{e}{4} \frac{\alpha^2}{j^2 - \beta^2 j} - \frac{e}{4} \frac{\beta^2}{j^2 - \alpha^2 j} \right) \\ &= \frac{e}{4} \frac{\alpha^2 - \beta^2}{j^2 - \beta^2 j} \end{aligned} \quad (C11)$$

For the pure Rashba system, we can take $\beta = 0$ in the $\alpha^2 > \beta^2$ condition. For the pure Dresselhaus system, we can take $\alpha = 0$ in the $\alpha^2 < \beta^2$ condition.

APPENDIX D: GAUGE INVARIANT POSITION OPERATOR

In this appendix, we shall consider a method to obtain the gauge invariant position operator and resolve the problem that the expectation value of the OAM depends on the choice of the eigenstates in the absence of applied electric field. In crystalline environment, the position operator cannot be simply set to $x = i\frac{\partial}{\partial k}$ [42]. We find that the OAM will depend on the choice of the eigenstates when we use the definition: $x = i\frac{\partial}{\partial k}$. For example, the following states can also be chosen as the eigenstates

$$|j, k; M\rangle = \frac{e^{iM\phi(k)}}{\sqrt{2}} \frac{1}{i} e^{i\phi(k)} \quad (D1)$$

where $M(k)$ is the phase factor and $n = 1$. It can be proved that the eigenstates of Eq. (D1) satisfy the relation $H_0 = \sum_n E_{nk} |j, k; M\rangle \langle j, k; M|$ where the eigenenergy E_{nk} is defined in Eq. (7). Using the eigenstates of Eq. (D1), the matrix element $\langle j, k; M | j_z | j, k; M \rangle$ is zero if $M = \pm 2$ but nonzero if $M = \pm 1$. Furthermore, if the eigenstates of Eq. (D1) are chosen, the signs of $\langle j, k; M | j_z | j, k; M \rangle$ and $\langle j, k; M | j_z | j, k; M \rangle$ will be different. Let us now consider the phase transformation of $|j, k; M\rangle = e^{i\phi(k)} |j, k; M\rangle$ where the phase $\phi(k)$ depends on band index n . We note that the eigenstates of Eq. (5) will be transformed to that of Eq. (D1) by the appropriate choice of the phase $\phi(k)$. Actually, we have $|j, k; M\rangle = (i)^j + ki$ and $|j, k; M\rangle = e^{i\phi(k)} |j, k; M\rangle$. Let us also introduce the operator $X^0 = x + A^0$ where $x = i\frac{\partial}{\partial k}$ and A^0 is the vector potential. Using the above gauge transformation [26], we obtain

$$\langle j, k; M | X^0 | j, k; M \rangle = \langle j, k; M | x | j, k; M \rangle + A^0 \frac{\partial \phi}{\partial k} \quad (D2)$$

Consider the specific transformation:

$$A^0 = A + \frac{\partial \phi}{\partial k} \quad (D3)$$

Eq. (D2) becomes the gauge invariant form [43]:

$$\langle j, k; M | X^0 | j, k; M \rangle = \langle j, k; M | x | j, k; M \rangle \quad (D4)$$

where the operator X is defined as $X = i\frac{\partial}{\partial k} + A$. We find that A^0 satisfies the transformation (D3) if A^0 is defined as

$$A_n^0 = \langle j, k; M | j_z | j, k; M \rangle \frac{\partial \phi}{\partial k} \quad (D5)$$

which is the Berry vector potential when the eigenstates $|j, k; M\rangle$ are used. The vector potential A in the eigenstates $|j, k; M\rangle$ can be defined as $A_n = \langle j, k; M | j_z | j, k; M \rangle \frac{\partial \phi}{\partial k}$ which generally depends on band index n . Therefore, the gauge invariant position operator X will depend on band index n :

$$X = i\frac{\partial}{\partial k} + A_n \quad (D6)$$

We find that the expectation value $\langle \mathbf{h} \mathbf{k} | \mathbf{X}_n | \mathbf{j} \mathbf{k} \rangle$ vanishes: $\langle \mathbf{h} \mathbf{k} | \mathbf{X}_n | \mathbf{j} \mathbf{k} \rangle = 0$. It can also be shown that $\langle \mathbf{h} \mathbf{k} | \mathbf{X}_n | \mathbf{j} \mathbf{k} \rangle = \langle \mathbf{h} \mathbf{k} | \mathbf{X}_n | \mathbf{j} \mathbf{k} \rangle$ by the use of $\langle \mathbf{h} \mathbf{k} | \mathbf{j} \mathbf{k} \rangle = \langle \mathbf{h} \mathbf{k} | \mathbf{j} \mathbf{k} \rangle$ where $\langle \mathbf{h} \mathbf{k} | \mathbf{j} \mathbf{k} \rangle$ is equal to unity for $n = n^0$ and zero for $n \neq n^0$. In terms of the gauge invariant position operator, the OAM operator $(\mathbf{x} \times \mathbf{k})_z$ is replaced by $(\mathbf{X}_n \times \mathbf{k})_z$. As a result, the expectation value of the OAM operator $\langle \mathbf{h} \mathbf{k} | \mathbf{X}_n | \mathbf{j} \mathbf{k} \rangle$ is zero for all the eigenstates in the absence of the applied electric field. Interestingly, note that the OAM operator does not always depend on band index n . For example, if the eigenstates of Eq. (5) are used, the Berry vector potential is independent of n , and so is the gauge invariant operator \mathbf{X}_n .

Let us now show that the calculated OAM Hall conductivities remain unchanged no matter whether the conventional \mathbf{x} or gauge invariant \mathbf{X}_n position operator is used. First of all, the gauge invariant velocity operator $\frac{1}{i\hbar} [\mathbf{X}_n; H_0(\mathbf{k})]$ is the same as the original one $\frac{1}{i\hbar} [\mathbf{x}; H_0(\mathbf{k})]$ because the vector potential \mathbf{A} commutes with $H_0(\mathbf{k})$, namely, $[\mathbf{A}; H_0(\mathbf{k})] = 0$. The gauge invariant OAM torque operator $\frac{1}{i\hbar} [(\mathbf{X}_n \times \mathbf{k})_z; H_0]$ is also

the same as the conventional one $\frac{1}{i\hbar} [(\mathbf{x} \times \mathbf{k})_z; H_0]$ because $(\mathbf{A} \times \mathbf{k})_z$ commutes with $H_0(\mathbf{k})$. Nevertheless, the OAM current operator $\frac{1}{2} \mathbf{f} \mathbf{v}_x; L_z g$ has an extra term of $(\mathbf{A} \times \mathbf{k})_z \mathbf{v}_x$ when the gauge invariant position operator \mathbf{X}_n is used. For the eigenstates of Eq. (11), we find that $\langle \mathbf{h} \mathbf{k} | \mathbf{M} | \mathbf{j} \mathbf{k} \rangle = \langle \mathbf{h} \mathbf{k} | \mathbf{M} | \mathbf{j} \mathbf{k} \rangle$ and $\langle \mathbf{h} \mathbf{k} | \mathbf{M} | \mathbf{j} \mathbf{k} \rangle = \langle \mathbf{h} \mathbf{k} | \mathbf{M} | \mathbf{j} \mathbf{k} \rangle$ and $\langle \mathbf{h} \mathbf{k} | \mathbf{M} | \mathbf{j} \mathbf{k} \rangle = \langle \mathbf{h} \mathbf{k} | \mathbf{M} | \mathbf{j} \mathbf{k} \rangle$ are all purely real [44]. On the other hand, Eq. (8) needs only the imaginary part of the matrix elements $\langle \mathbf{h} \mathbf{k} | \mathbf{M} | \mathbf{j} \mathbf{k} \rangle$ and $\langle \mathbf{h} \mathbf{k} | \mathbf{M} | \mathbf{j} \mathbf{k} \rangle$. This shows that the extra term $(\mathbf{A} \times \mathbf{k})_z \mathbf{v}_x$ does not contribute to the Kubo formula. In general, using $\mathbf{j} \mathbf{k} = e^{i\mathbf{n} \cdot \mathbf{r}} \mathbf{j} \mathbf{k}$, we have $\langle \mathbf{h} \mathbf{k} | \mathbf{j} \mathbf{k} \rangle = \langle \mathbf{h} \mathbf{k} | \mathbf{j} \mathbf{k} \rangle$ and $\langle \mathbf{h} \mathbf{k} | \mathbf{j} \mathbf{k} \rangle = \langle \mathbf{h} \mathbf{k} | \mathbf{j} \mathbf{k} \rangle$. With the eigenstates of Eq. (21), we obtain that $\langle \mathbf{h} \mathbf{k} | \mathbf{j} \mathbf{k} \rangle = \langle \mathbf{h} \mathbf{k} | \mathbf{j} \mathbf{k} \rangle$ and $\langle \mathbf{h} \mathbf{k} | \mathbf{j} \mathbf{k} \rangle = \langle \mathbf{h} \mathbf{k} | \mathbf{j} \mathbf{k} \rangle$ are all purely real. Therefore, we conclude that the OAM Hall conductivities σ_{xy}^0 and σ_{xy}^0 remain the same even if we replace \mathbf{x} with \mathbf{X}_n or \mathbf{X}_n .

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- [1] G. A. Prinz, Science 282, 1660 (1998); S. A. Wolf, D. D. Awschalom, R. A. Buhrman, J. M. Doughton, S. von Molnar, M. L. Roukes, A. Y. Chtchelkanova, and D. M. Treger, Science 294, 1488 (2001).
- [2] I. Zutic, J. Fabian, and S. D. Samra, Rev. Mod. Phys. 76, 323 (2004).
- [3] S. Murakami, N. Nagaosa, and S.-C. Zhang, Science 301, 1348 (2003).
- [4] J. Sinova, D. Culcer, Q. Niu, N. A. Sinitsyn, T. Jungwirth, and A. H. MacDonald, Phys. Rev. Lett. 92, 126603 (2004).
- [5] M. I. Dyakonov and V. I. Perel, Sov. Phys. JETP 33, 1053 (1971); L. S. Levitov, Yu. V. Nazarov, and G. M. Eliashberg, Sov. Phys. JETP 61, 133 (1985); J. E. Hirsch, Phys. Rev. Lett. 83, 1834 (1999); S. Zhang, Phys. Rev. Lett. 85, 393 (2000); L. I. M. Agarril, A. V. Chablik, and M. V. Entin, Semiconductors 35, 1081 (2001).
- [6] D. Culcer, Jairo Sinova, N. A. Sinitsyn, T. Jungwirth, A. H. MacDonald, and Q. Niu, Phys. Rev. Lett. 93, 46602 (2004).
- [7] S. Zhang, and Z. Yang, Phys. Rev. Lett. 94, 66602 (2005).
- [8] G. Y. Guo, Y. Yao, and Q. Niu, Phys. Rev. Lett. 94, 226601 (2005).
- [9] J.-I. Inoue, G. E. W. Bauer, and L. W. Molenkamp, Phys. Rev. B 70, 041303(R) (2004); S. Murakami, Phys. Rev. B 69, 241202(R) (2004); E. G. Mishchenko, A. V. Shytov, and B. I. Halperin, Phys. Rev. Lett. 93, 226602 (2004); K. Nomura, Jairo Sinova, T. Jungwirth, Q. Niu, and A. H. MacDonald, Phys. Rev. B 71, 041304 (2005); R. Raimondi, and P. Schwab, Phys. Rev. B 71, 33311 (2005); A. Khaetskii, Phys. Rev. Lett. 96, 56602 (2006).
- [10] O. V. D. M. Itrova, Phys. Rev. B 71, 245327 (2005).
- [11] O. Chalaev and Daniel Loss, Phys. Rev. B 71, 245318 (2005).
- [12] J. Wunderlich, B. K. Aestner, J. Sinova, and T. Jungwirth, Phys. Rev. Lett. 94, 47204 (2005).
- [13] Y. K. Kato, R. C. Myers, A. C. Gossard, and D. D. Awschalom, Science 306, 1910 (2004).
- [14] P.-Q. Jin, Y.-Q. Li, F. C. Zhang, cond-mat/0502231 (2005).
- [15] Q. F. Sun and X. C. Xie, Phys. Rev. B 72, 245305 (2005).
- [16] P. Zhang, J. Shi, D. Xiao, and Q. Niu, cond-mat/0503505 (2005); J. Shi, P. Zhang, D. Xiao, and Q. Niu, Phys. Rev. Lett. 96, 76604 (2006).
- [17] J. Wang, B. G. Wang, W. Ren, and H. Guo, cond-mat/0507159 (2005).
- [18] Y. Wang, K. Xia, Z.-B. Su, and Z. Ma, Phys. Rev. Lett. 96, 66601 (2006).
- [19] Y. A. Bychkov and E. I. Rashba, J. Phys. C 17, 6039 (1984).
- [20] G. Dresselhaus, Phys. Rev. 100, 580 (1955).
- [21] J. Nitta, T. Akazaki, H. Takayanagi, and T. Enoki, Phys. Rev. Lett. 78, 1335 (1997).
- [22] M. Marder, Condensed Matter Physics (John Wiley & Sons, Inc., New York, 2000).
- [23] S.-Q. Shen, Phys. Rev. B 70, 081311(R) (2004).
- [24] N. A. Sinitsyn, E. M. Hankiewicz, W. Teizer, and J. Sinova, Phys. Rev. B 70, 81312(R) (2004).
- [25] M. V. Berry, Proc. Soc. Lond. A 392, 45 (1984).
- [26] A. Bohm, A. Mostafazadeh, H. Koizumi, Q. Niu and J. Zwanziger, The Geometric Phase in Quantum Systems (Springer, Berlin, 2003).
- [27] J. Zak, Phys. Rev. Lett. 62, 2747 (1989).
- [28] M. C. Chang, Q. Niu, Phys. Rev. Lett. 75, 1348 (1995); M. C. Chang, Q. Niu, Phys. Rev. B 53, 7010 (1996).
- [29] S. Murakami, Naoto Nagaosa, S. C. Zhang, Phys. Rev. B 69, 235206 (2004).
- [30] We evaluate σ_{yx}^0 and σ_{yx}^0 directly, and find the relations of $\sigma_{xy}^0 = \sigma_{yx}^0$ and $\sigma_{xy}^0 = \sigma_{yx}^0$.
- [31] D. Schmeltzer, cond-mat/0509607 (2005).

- [32] M . C . Chang, Phys. Rev. B 71, 085315 (2005).
- [33] J. Hu, cond-mat/0503149 (2005).
- [34] J. Li, L. Hu, S.-Q . Shen, Phys. Rev. B 71, 241305(R) (2005).
- [35] B . K . Nikolic, L . P . Zarbo, and S . W elack, Phys. Rev. B 72, 75335 (2005).
- [36] J . J . Sakurai, Advanced Quantum Mechanics (Addison Wesley, 1997).
- [37] F . M eier and D . Loss, Phys. Rev. Lett. 90, 167204 (2004).
- [38] N . Sugimoto, S . Onoda, S . Murakami and N . Nagaosa, Phys. Rev. B 73, 113305 (2006).
- [39] J . Schliemann, J . C . Egues, and D . Loss, Phys. Rev. Lett. 90, 146801 (2003).
- [40] S . D . Ganichev, V . V . Bel'kov, L . E . Golub, E . L . Ivchenko, Petra Schneider, S . G iglberger, J . Ermons, J . De Boeck, G . Borghs, W . Wegscheider, D . Weiss, and W . Prettel, Phys. Rev. Lett. 92, 256601 (2004).
- [41] G . Arfken and H . J . Weber, Mathematical Methods for Physicists (Academic Press, 1995).
- [42] E . I . Blount: Formalisms of Band Theory in Solid State Physics 13, 305, (Academic, New York 1962) edited by F . Seitz and D . Turnbull.
- [43] J . J . Sakurai, Modern Quantum Mechanics (Addison Wesley, 1994).
- [44] In general, it can be proved that $\text{Im} \langle j | \frac{\partial}{\partial k} | j \rangle$ is purely imaginary by means of $\text{Im} \langle j | j \rangle = 1$ (see Ref. 26). In our definition of $A_n = \text{Im} \langle j | \frac{\partial}{\partial k} | j \rangle$, however, A_n is purely real.